

CLAIMS

1. A method for forming a pattern comprising the steps
of:

forming a first region and a second region;

5 discharging a composition containing a pattern formation
material to a region across the second region and the first
region; and

 flowing a part of the composition discharged to the first
region into the second region;

10 wherein wettability of the first region with respect to
the composition is lower than wettability of the second region
with respect to the composition.

2. A method for forming a pattern comprising the steps
15 of:

forming selectively a mask over a substrate;

forming a first region by using the mask;

forming a second region by removing the mask;

 discharging a composition containing a pattern formation
20 material to a region across the second region and the first
region; and

 flowing a part of the composition discharged to the first
region into the second region;

 wherein wettability of the first region with respect to
25 the composition is lower than wettability of the second region

with respect to the composition.

3. A method for forming a pattern comprising the steps of:

5 forming selectively a photocatalytic substance over a substrate;

 forming a first region over the substrate and the photocatalytic substance;

 emitting light to the photocatalytic substance to form
10 a second region;

 discharging a composition containing a pattern formation material to a region across the second region and the first region; and

 flowing a part of the composition discharged to the first
15 region into the second region;

 wherein wettability of the first region with respect to the composition is lower than wettability of the second region with respect to the composition.

20 4. A method for forming a pattern comprising the steps of:

 forming a first region over a substrate;

 emitting light selectively to the first region to form
a second region;

25 discharging a composition containing a pattern formation

material to a region across the second region and the first region; and

flowing a part of the composition discharged to the first region into the second region;

5 wherein wettability of the first region with respect to the composition is lower than wettability of the second region with respect to the composition.

5. The method for forming the pattern according to any
10 one of Claims 1 to 4, wherein a first region is formed by forming a substance having a fluorocarbon chain.

6. The method for forming the pattern according to Claim
3, wherein the photocatalytic substance is formed by using
15 titanium oxide.

7. A method for manufacturing a thin film transistor comprising the steps of:

forming a first region and a second region;

20 discharging a composition containing a conductive material to a region across the second region and the first region; and

flowing a part of the composition discharged to the first region into the second region to form an electrode layer;

25 wherein wettability of the first region with respect to

the composition is lower than wettability of the second region with respect to the composition.

8. A method for manufacturing a thin film transistor
5 comprising the steps of:

forming a first region and a second region;

discharging a composition containing a first conductive material to a region across the first region and the second region;

10 flowing a part of the composition discharged to the first region into the second region to form an electrode layer; and

discharging a second conductive material to the second region to be in contact with the electrode layer to form a wiring layer;

15 wherein wettability of the first region with respect to the composition is lower than wettability of the second region with respect to the composition.

9. A method for forming a pattern comprising the steps
20 of:

forming selectively a photocatalytic substance over a substrate;

forming a first region over the substrate and the photocatalytic substance;

25 emitting light to the photocatalytic substance to form

a second region;

discharging a composition containing a conductive material to a region across the first region and the second region; and

5 flowing a part of the composition discharged to the first region into the second region to form an electrode layer;

wherein wettability of the first region with respect to the composition is lower than wettability of the second region with respect to the composition.

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10. The method for manufacturing the thin film transistor according to any one of Claims 7 to 9, wherein the first region is formed by forming a substance having a fluorocarbon chain.

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11. The method for manufacturing the thin film transistor according to Claim 9, wherein titanium oxide is formed as the photocatalytic substance.

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12. A method for manufacturing a display device using the thin film transistor manufactured by the method according to Claim 7 or 9, wherein the electrode layer is formed as a gate electrode layer.

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13. A method for manufacturing a display device using the thin film transistor manufactured by the method according to

Claim 8, wherein the electrode layer is formed as a gate electrode layer and the wiring layer is formed as a gate wiring layer.

- 5 14. A method for manufacturing a thin film transistor comprising the steps of:
- forming a first region and a second region over a substrate;
- discharging a composition containing a mask formation
10 material to a region across the first region and the second region;
- flowing a part of the composition containing the mask formation material discharged to the first region into the second region to form a mask;
- 15 changing a part of the first region by using the mask to form a third region;
- forming a fourth region by removing the mask;
- discharging a composition containing a conductive material to a region across the third region and the fourth
20 region; and
- flowing the composition in the fourth region into the third region to form a first electrode layer and a second electrode layer;
- wherein wettability of the first region with respect to
25 the composition containing the mask formation material is lower

wettability that of the second region with respect to the composition containing the mask formation material, and wettability of the fourth region with respect to the conductive material is lower than wettability of the third region with
5 respect to the conductive material.

15. The method for manufacturing the thin film transistor according to Claim 14, wherein the first region is formed by forming a substance having fluorocarbon.

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16. A method for manufacturing a display device using the thin film transistor manufactured by the method according to Claim 12, wherein each of the first electrode layer and the second electrode layer is formed as a source electrode layer
15 or a drain electrode layer.

17. A thin film transistor comprising:
a wiring layer provided over a substrate; and
an electrode layer being in contact with the wiring layer;
20 wherein the wiring layer is formed on a first region, the electrode layer is formed on a second region, and wettability of the second region with respect to the electrode layer and the wiring layer is lower than wettability with respect to the electrode layer and the wiring layer of the first region.

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18. The thin film transistor according to Claim 17,
wherein the electrode layer has a smaller width and a
thinner thickness than those of the wiring layer.

5 19. A display device comprising:
a wiring layer provided over a substrate; and
an electrode layer being in contact with the wiring layer;
wherein the wiring layer is formed on a first region, the
electrode layer is formed on a second region, and wettability
10 of the second region with respect to the electrode layer and
the wiring layer is lower than wettability of the first region
with respect to the electrode layer and the wiring layer.

20. The display device according to Claim 19,
15 wherein the electrode layer has a smaller width and a
thinner thickness than those of the wiring layer.

21. A television device comprising:
a wiring layer provided over a substrate; and
20 an electrode layer being in contact with the wiring layer;
wherein the wiring layer is formed on a first region, the
electrode layer is formed on a second region, and wettability
of the second region with respect to the electrode layer and
the wiring layer is lower than wettability of the first region
25 with respect to the electrode layer and the wiring layer.

22. The television device according to Claim 21,
wherein the electrode layer has a smaller width and a
thinner thickness than those of the wiring layer..